

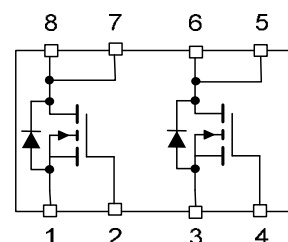
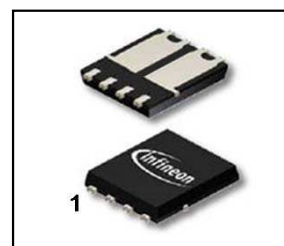
OptiMOS™-T2 Power-Transistor

Product Summary

V_{DS}	100	V
$R_{DS(on),max}^{4)}$	35	mΩ
I_D	20	A

Features

- Dual N-channel Logic Level - Enhancement mode
- AEC Q101 qualified
- MSL1 up to 260°C peak reflow
- 175°C operating temperature
- Green Product (RoHS compliant)
- 100% Avalanche tested
- Feasible for automatic optical inspection (AOI)

PG-TDSON-8-10


Type	Package	Marking
IPG20N10S4L-35A	PG-TDSON-8-10	4N10L35

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current one channel active	I_D	$T_C=25\text{ °C}$, $V_{GS}=10\text{ V}^{1)}$	20	A
		$T_C=100\text{ °C}$, $V_{GS}=10\text{ V}^{2)}$	17	
Pulsed drain current ²⁾ one channel active	$I_{D,pulse}$	-	80	
Avalanche energy, single pulse ^{2, 4)}	E_{AS}	$I_D=10\text{ A}$	60	mJ
Avalanche current, single pulse ⁴⁾	I_{AS}	-	15	A
Gate source voltage	V_{GS}	-	±16	V
Power dissipation one channel active	P_{tot}	$T_C=25\text{ °C}$	43	W
Operating and storage temperature	T_j, T_{stg}	-	-55 ... +175	°C

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal characteristics²⁾						
Thermal resistance, junction - case	R_{thJC}	-	-	-	3.5	K/W
SMD version, device on PCB	R_{thJA}	minimal footprint	-	100	-	
		6 cm ² cooling area ³⁾	-	60	-	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	100	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=16\mu\text{A}$	1.1	1.6	2.1	
Zero gate voltage drain current ⁴⁾	I_{DSS}	$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.01	1	μA
		$V_{DS}=100\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}^{2)}$	-	1	100	
Gate-source leakage current ⁴⁾	I_{GSS}	$V_{GS}=16\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance ⁴⁾	$R_{DS(on)}$	$V_{GS}=4.5\text{ V}, I_D=10\text{ A}$	-	38	45	m Ω
		$V_{GS}=10\text{ V}, I_D=17\text{ A}$	-	29	35	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics²⁾

Input capacitance ⁴⁾	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	850	1105	pF
Output capacitance ⁴⁾	C_{oss}		-	285	370	
Reverse transfer capacitance ⁴⁾	C_{rss}		-	30	60	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=50\text{ V}, V_{GS}=10\text{ V},$ $I_D=20\text{ A}, R_G=11\ \Omega$	-	3	-	ns
Rise time	t_r		-	2	-	
Turn-off delay time	$t_{d(off)}$		-	18	-	
Fall time	t_f		-	13	-	

Gate Charge Characteristics^{2, 4)}

Gate to source charge	Q_{gs}	$V_{DD}=80\text{ V}, I_D=20\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	2.9	3.8	nC
Gate to drain charge	Q_{gd}		-	3.2	6.4	
Gate charge total	Q_g		-	13.4	17.4	
Gate plateau voltage	$V_{plateau}$		-	3.5	-	V

Reverse Diode

Diode continuous forward current ²⁾ one channel active	I_S	$T_C=25\text{ }^\circ\text{C}$	-	-	20	A
Diode pulse current ²⁾ one channel active	$I_{S,pulse}$		-	-	80	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=17\text{ A},$ $T_J=25\text{ }^\circ\text{C}$	-	1.0	1.3	V
Reverse recovery time ²⁾	t_{rr}	$V_R=50\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	50	-	ns
Reverse recovery charge ^{2, 4)}	Q_{rr}		-	75	-	nC

¹⁾ Current is limited by bondwire; with an $R_{thJC} = 3.5\text{K/W}$ the chip is able to carry 24A at 25°C.

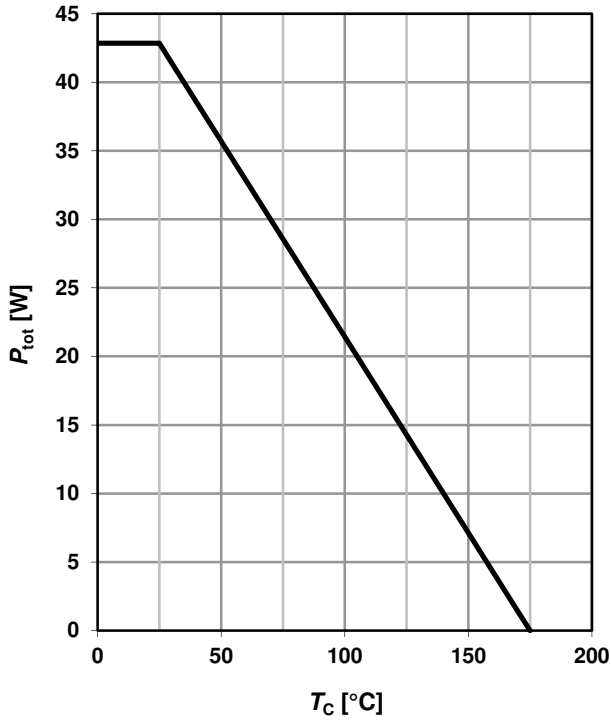
²⁾ Specified by design. Not subject to production test.

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical in still air.

⁴⁾ Per channel

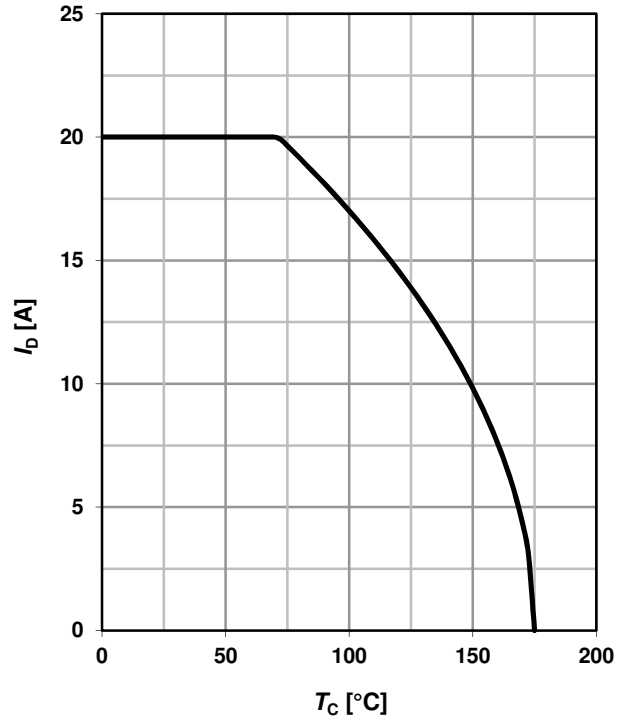
1 Power dissipation

$P_{tot}=f(T_C)$; $V_{GS} \geq 6$ V; one channel active



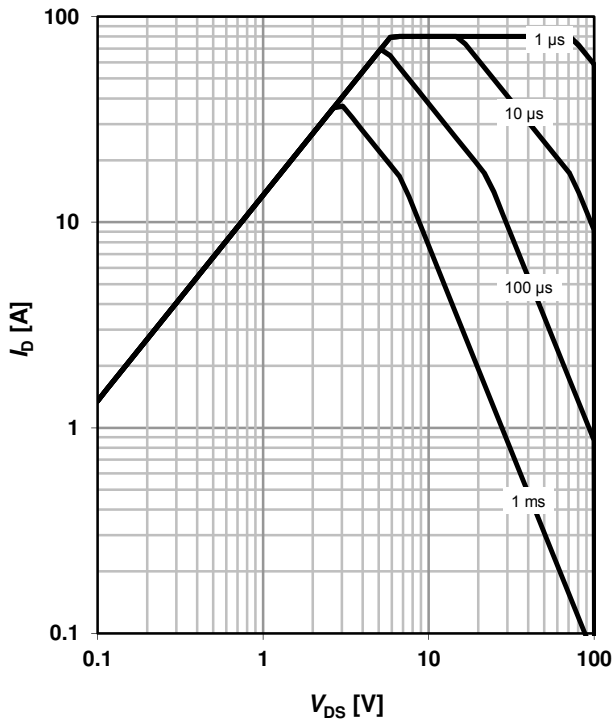
2 Drain current

$I_D=f(T_C)$; $V_{GS} \geq 6$ V; one channel active



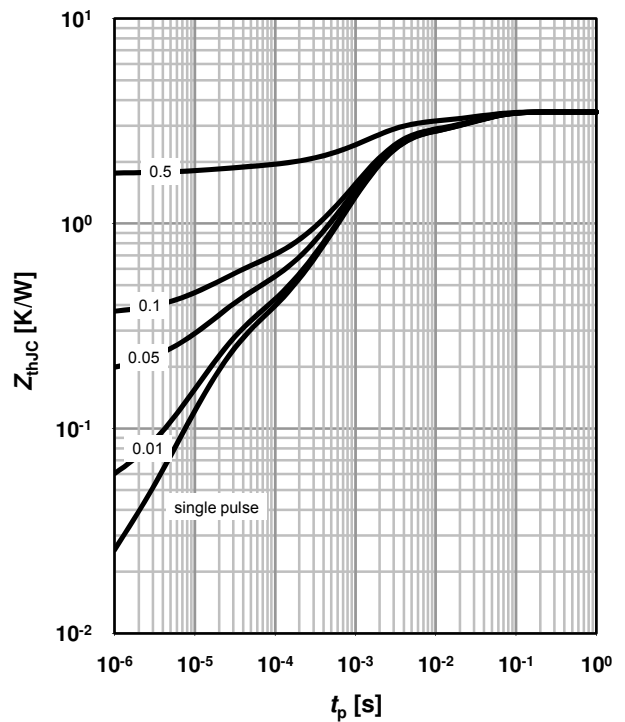
3 Safe operating area

$I_D=f(V_{DS})$; $T_C=25^\circ\text{C}$; $D=0$; one channel active
parameter: t_p



4 Max. transient thermal impedance

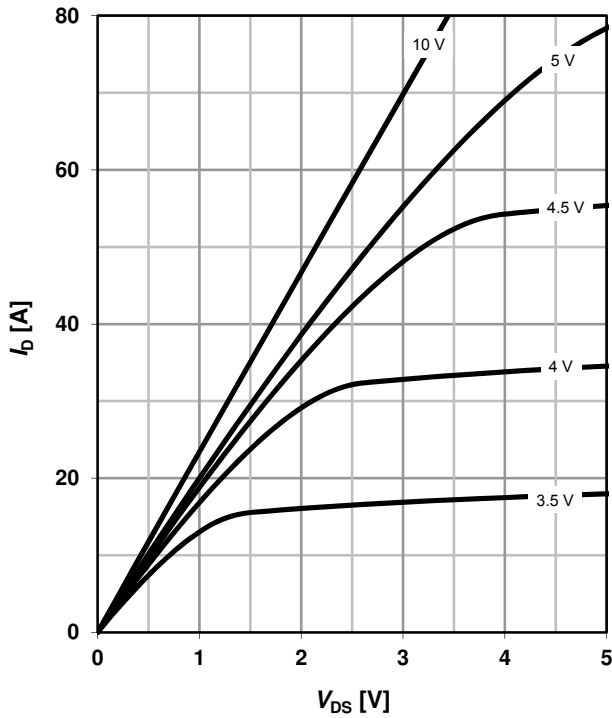
$Z_{thJC}=f(t_p)$
parameter: $D=t_p/T$



5 Typ. output characteristics⁵⁾

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

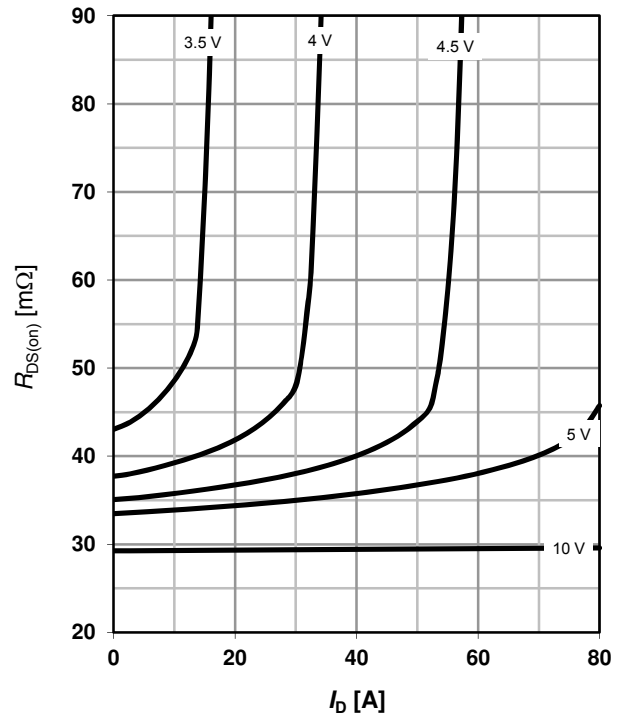
parameter: V_{GS}



6 Typ. drain-source on-state resistance⁵⁾

$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

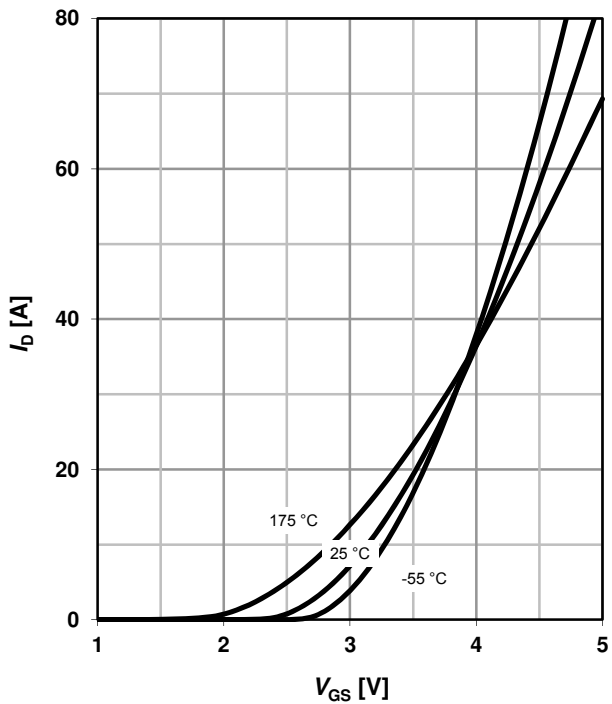
parameter: V_{GS}



7 Typ. transfer characteristics⁵⁾

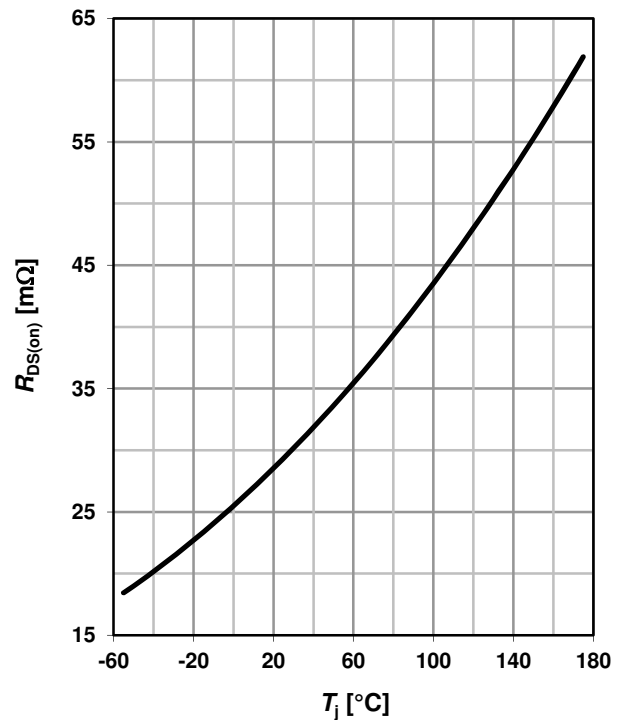
$I_D = f(V_{GS}); V_{DS} = 6\text{V}$

parameter: T_j



8 Typ. drain-source on-state resistance⁵⁾

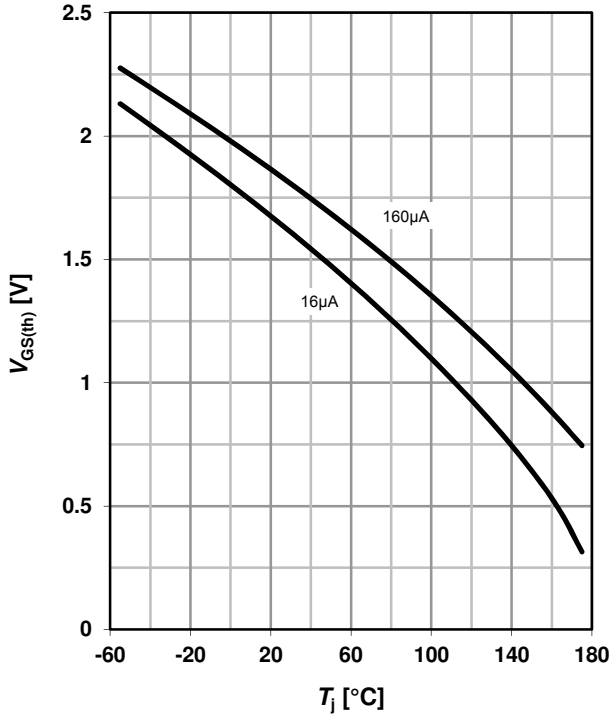
$R_{DS(on)} = f(T_j); I_D = 17\text{A}; V_{GS} = 10\text{V}$



9 Typ. gate threshold voltage

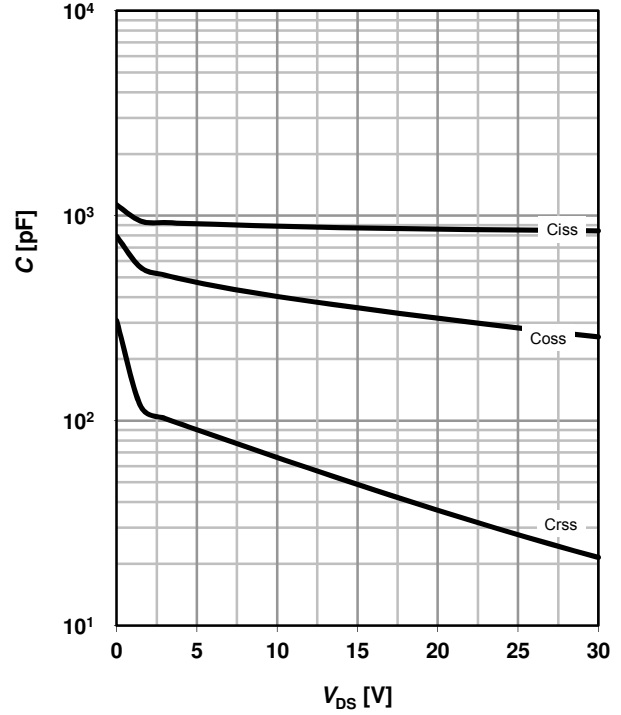
$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$

parameter: I_D



10 Typ. Capacitances⁵⁾

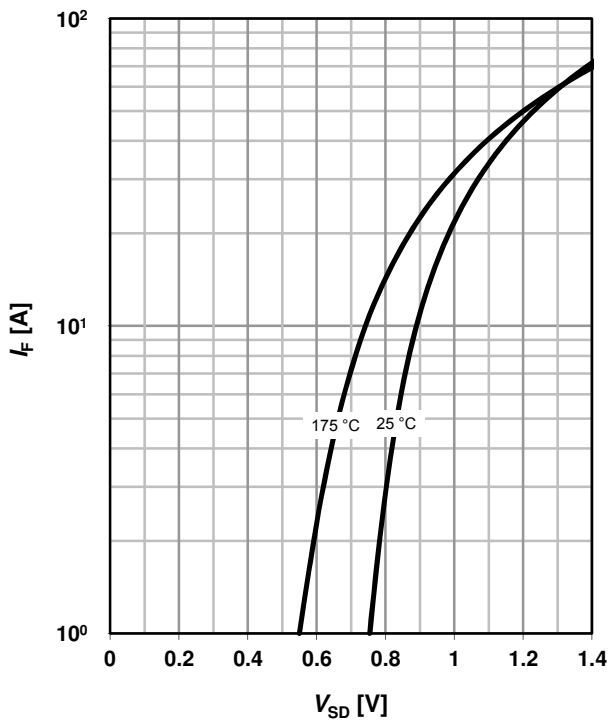
$C = f(V_{DS}); V_{GS} = 0V; f = 1MHz$



11 Typical forward diode characteristics⁵⁾

$I_F = f(V_{SD})$

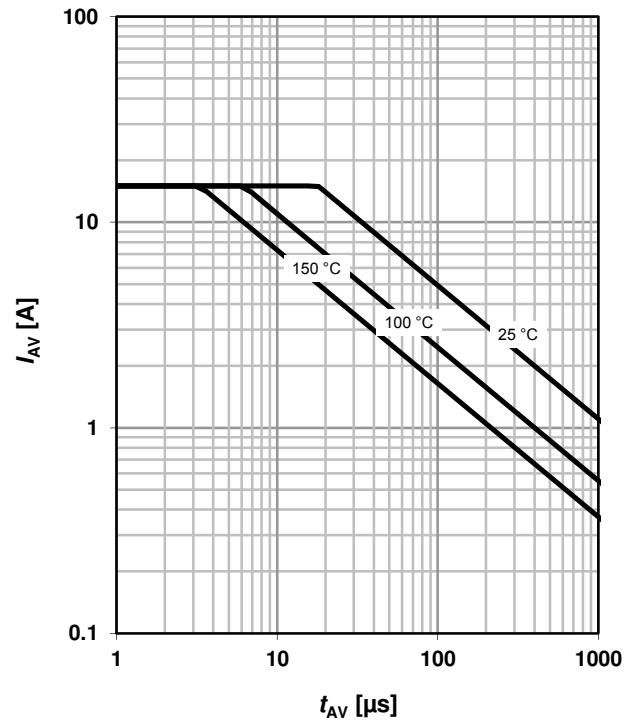
parameter: T_j



12 Avalanche characteristics⁵⁾

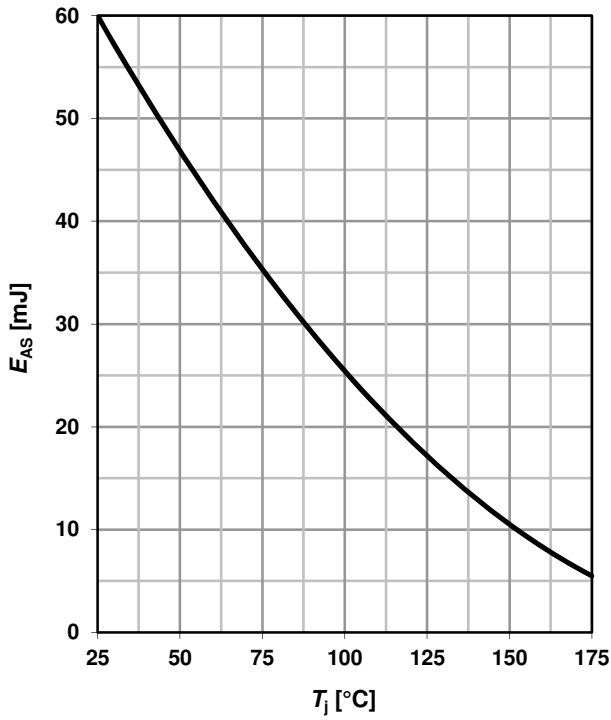
$I_{AS} = f(t_{AV})$

parameter: $T_{j(start)}$



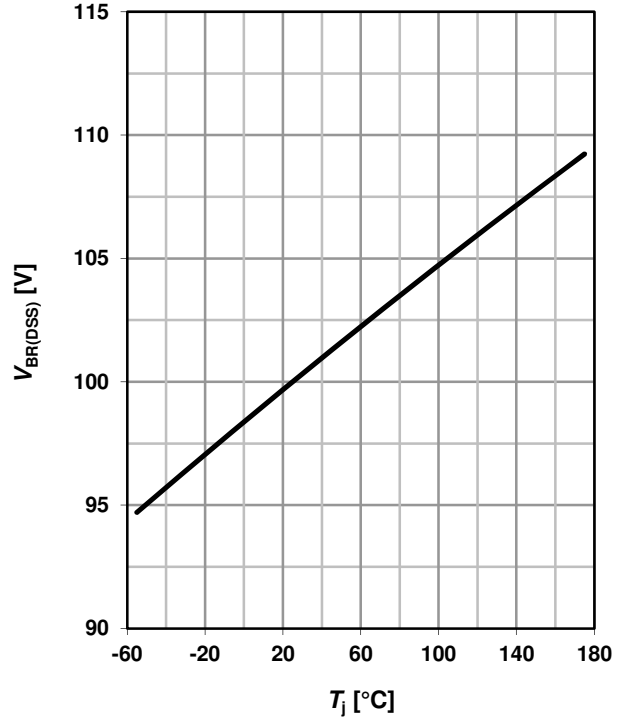
13 Avalanche energy⁵⁾

$E_{AS}=f(T_j), I_D=10A$



14 Drain-source breakdown voltage

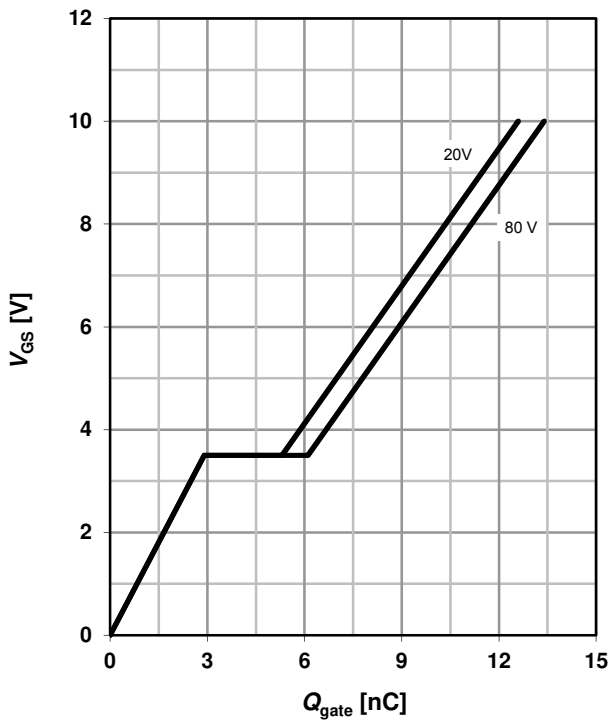
$V_{BR(DSS)}=f(T_j); I_D=1mA$



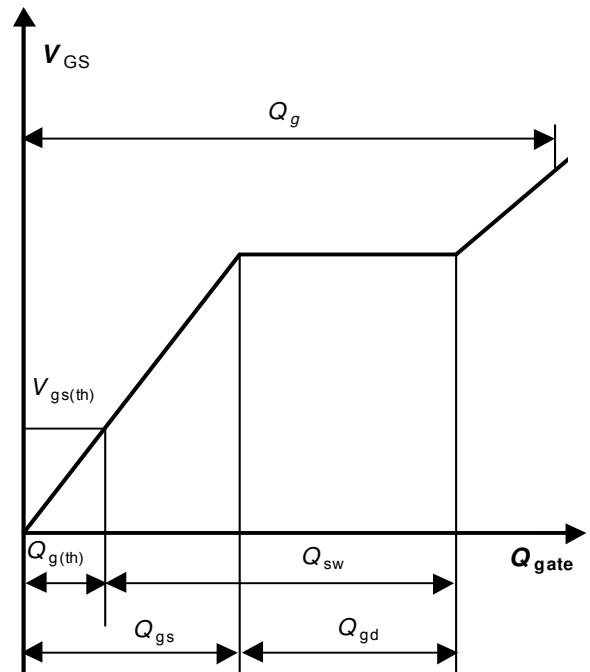
15 Typ. gate charge⁵⁾

$V_{GS}=f(Q_{gate}); I_D=20A$ pulsed

parameter: V_{DD}



16 Gate charge waveforms



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If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.

Revision History

Version	Date	Changes
Revision 1.0	04.03.2013	Final Data Sheet